**Product data sheet** 

## 1. General description

NPN low  $V_{CEsat}$  transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS9110T

### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability: I<sub>C</sub> and I<sub>CM</sub>
- AEC-Q101 qualified

## 3. Applications

- Major application segments
  - Automotive 42 V power
  - · Telecom infrastructure
  - Industrial
- Power management
  - · DC/DC converters
  - Supply line switching
  - Battery charger
  - LCD backlighting
- Peripheral drivers
  - Driver in low supply voltage applications (e.g. lamps and LEDs)
  - · Inductive load driver (e.g. relays, buzzers and motors)

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	100	V
I <sub>C</sub>	collector current		-	-	1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	3	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 1 A; $I_B$ = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	165	200	mΩ



100 V, 1 A NPN low VCEsat transistor

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	С
2	Е	emitter		j
3	С	collector		В — 🛴
				    E
			1	sym123
			SOT23	

## 6. Ordering information

## **Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
PBSS8110T	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PBSS8110T	%U8

<sup>[1] % =</sup> placeholder for manufacturing site code

# 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

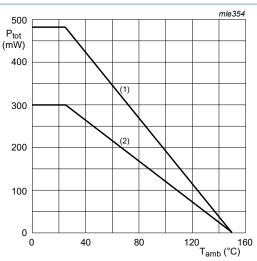
Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	120	V
$V_{CEO}$	collector-emitter voltage	open base		-	100	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	5	V
I <sub>C</sub>	collector current			-	1	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	3	А
I <sub>B</sub>	base current			-	300	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
			[2]	-	480	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

PBSS8110T

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

### 100 V, 1 A NPN low VCEsat transistor



- (1) FR4 PCB; 1 cm<sup>2</sup> copper mounting pad for collector.
- (2) Standard footprint.

Fig. 1. Power derating curves

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ιτη-α <i>)</i>	thermal resistance from	in free air	[1]	-	-	417	K/W
	junction to ambient		[2]	-	-	260	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

#### 100 V, 1 A NPN low VCEsat transistor

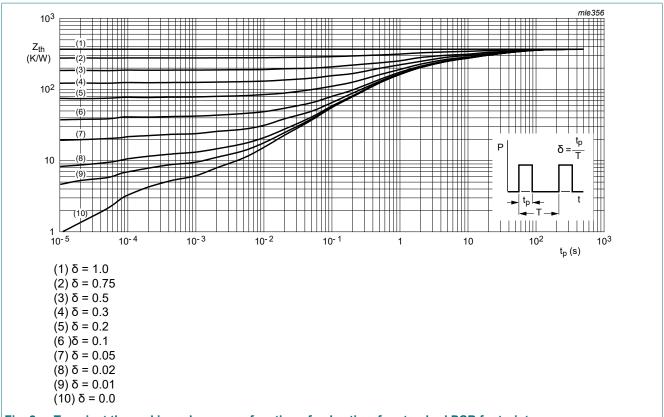
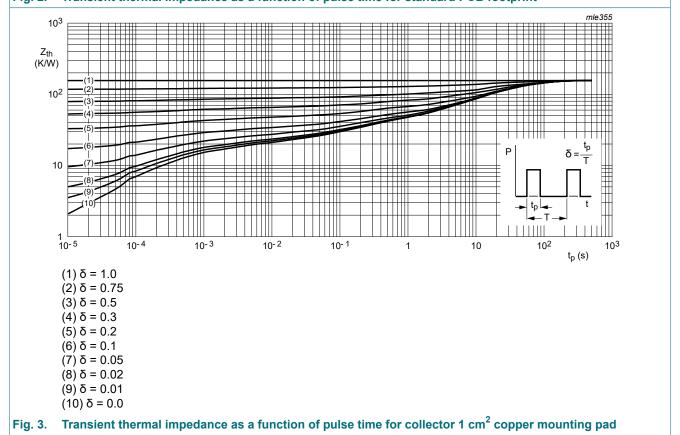


Fig. 2. Transient thermal impedance as a function of pulse time for standard PCB footprint



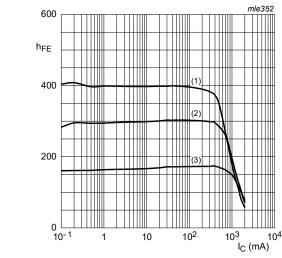
## 100 V, 1 A NPN low VCEsat transistor

# 10. Characteristics

## **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_C = 100 \ \mu\text{A}; \ I_E = 0 \ \text{A}; \ T_{amb} = 25 \ ^{\circ}\text{C}$	120	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C$ = 10 mA; $I_B$ = 0 A; pulsed; $t_p \le 300$ µs; $\delta \le 0.02$ ;; $T_{amb}$ = 25 °C	100	-	-	V
V <sub>(BR)EBO</sub>	emitter-base breakdown voltage (collector open)	$I_E = 100 \ \mu\text{A}; \ I_C = 0 \ \text{A}; \ T_{amb} = 25 \ ^{\circ}\text{C}$	5	-	-	V
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 80 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 80 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 80 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 1 mA; T <sub>amb</sub> = 25 °C	150	-	-	
		V <sub>CE</sub> = 10 V; I <sub>C</sub> = 250 mA; T <sub>amb</sub> = 25 °C	150	-	500	
		$V_{CE}$ = 10 V; $I_{C}$ = 500 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	100	-	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 1 A; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	80	-	-	
V <sub>CEsat</sub>	collector-emitter	I <sub>C</sub> = 100 mA; I <sub>B</sub> = 10 mA; T <sub>amb</sub> = 25 °C	-	-	40	mV
	saturation voltage	I <sub>C</sub> = 500 mA; I <sub>B</sub> = 50 mA; T <sub>amb</sub> = 25 °C	-	-	120	mV
		$I_C$ = 1 A; $I_B$ = 100 mA; pulsed; $t_p \le$	-	-	200	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	165	200	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 1 A; I <sub>B</sub> = 100 mA; T <sub>amb</sub> = 25 °C	-	-	1.05	V
$V_{BEon}$	base-emitter turn-on voltage	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 1 A; T <sub>amb</sub> = 25 °C	-	-	0.9	V
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 50 mA; f = 100 MHz; $T_{amb}$ = 25 °C	100	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_{E} = 0 \text{ A}; i_{e} = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25  ^{\circ}\text{C}$	-	-	7.5	pF

#### 100 V, 1 A NPN low VCEsat transistor

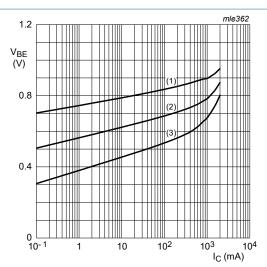


(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 4. DC current gain as a function of collector current; typical values

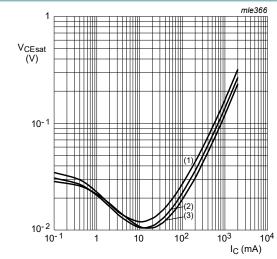


$$V_{CF} = 10 \text{ V}$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 5. Base-emitter voltage as a function of collector current; typical values



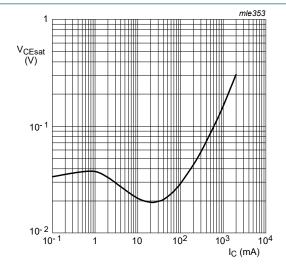
$$I_{\rm C}/I_{\rm B} = 10$$

$$(1) T_{amb} = 100 °C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Collector-emitter saturation voltage as a Fig. 6. function of collector current; typical values



$$I_C/I_B = 20$$
  
 $T_{amb} = 25 °C$ 

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

#### 100 V, 1 A NPN low VCEsat transistor

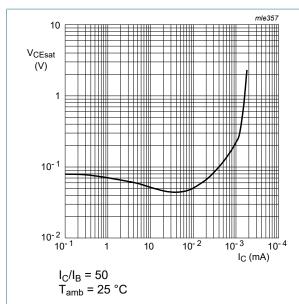
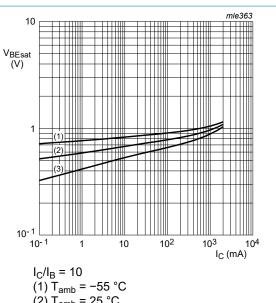
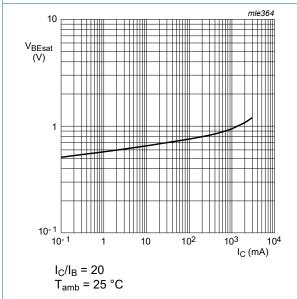


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



 $I_{C}/I_{B} = 10$ (1)  $T_{amb} = -55 \,^{\circ}C$ (2)  $T_{amb} = 25 \,^{\circ}C$ (3)  $T_{amb} = 100 \,^{\circ}C$ 

Fig. 9. Base-emitter saturation voltage as a function of collector current; typical values



collector current; typical values

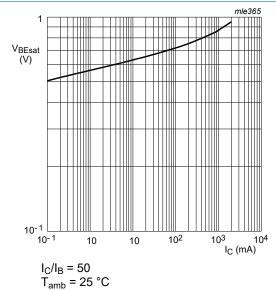
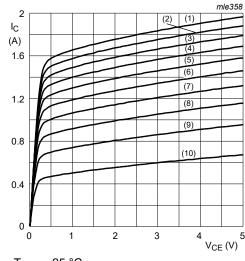


Fig. 10. Base-emitter saturation voltage as a function of collector current; typical values

#### 100 V, 1 A NPN low VCEsat transistor



T<sub>amb</sub> = 25 °C

(1)  $I_B = 3500 \, \mu A$ 

 $(2) I_B = 3150 \mu A$ (3)  $I_B = 2800 \,\mu A$ 

(4)  $I_B = 2450 \mu A$ 

(5)  $I_B = 2100 \mu A$ 

(6)  $I_B = 1750 \mu A$ 

 $(7) I_B = 1400 \mu A$ 

(8)  $I_B = 1050 \,\mu A$  $(9) I_B = 700 \mu A$ 

 $(10) I_B = 350 \mu A$ 

Fig. 12. Collector current as a function of collector-

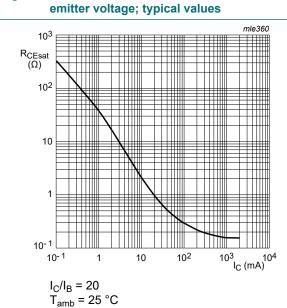
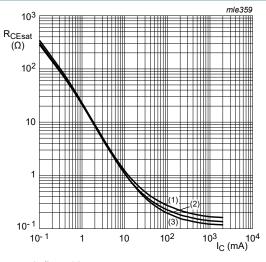


Fig. 14. Collector-emitter equivalent on-resistance as a function of collector current; typical values



I<sub>C</sub>/I<sub>B</sub> = 10 (1) T<sub>amb</sub> = 100 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -55 °C

Fig. 13. Collector-emitter equivalent on-resistance as a function of collector current; typical values

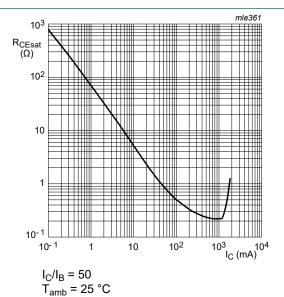


Fig. 15. Collector-emitter equivalent on-resistance as a function of collector current; typical values

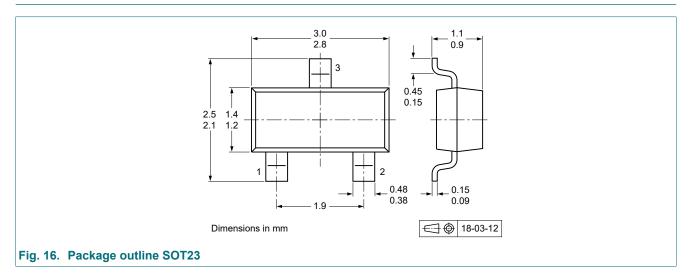
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## 11. Test information

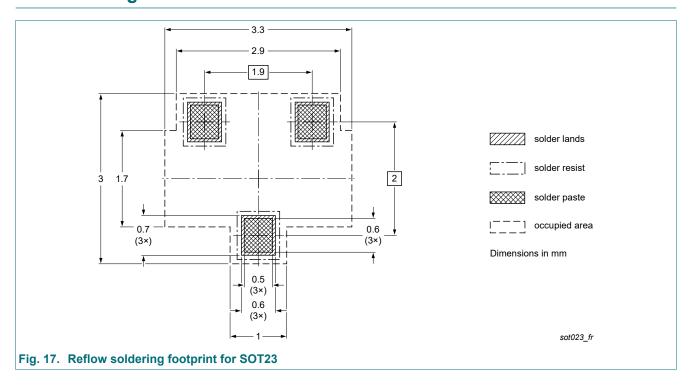
#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

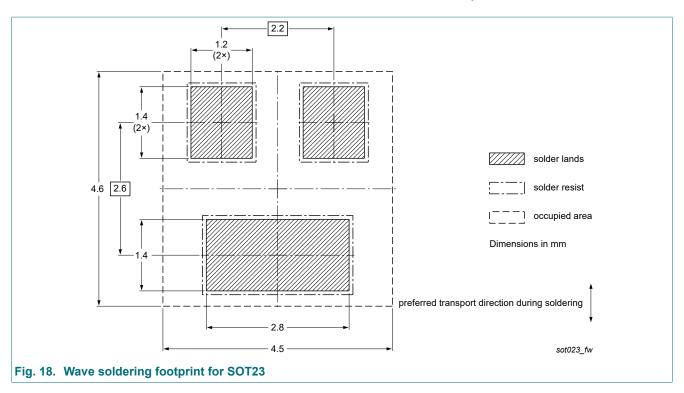
# 12. Package outline



## 13. Soldering



## 100 V, 1 A NPN low VCEsat transistor



## 100 V, 1 A NPN low VCEsat transistor

# 14. Revision history

### **Table 8. Revision history**

Table of Novicion motory								
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PBSS8110T v.3	20220513	Product data sheet	-	PBSS8110T v.2				
Modifications:	Nexperia.	ta sheet has been redesi n adapted to the new cor		7.0				
PBSS8110T v.2	20031222	Product data sheet	-	PBSS8110T v.1				
PBSS8110T v.1	20030728	Product data sheet	-	-				

### 100 V, 1 A NPN low VCEsat transistor

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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